

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sumakeris et al.

Serial No.: To Be Assigned

Filed: Concurrently Herewith

For: METHODS OF FORMING POWER SEMICONDUCTOR DEVICES USING BOULE-GROWN SILICON CARBIDE DRIFT LAYERS AND POWER SEMICONDUCTOR DEVICES FORMED THEREBY

Date: October 16, 2003

Mail Stop Patent Application

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,


Grant A. Scott
Registration No. 36,925

Myers Bigel Sibley & Sajovec, P.A.

P. O. Box 37428

Raleigh, North Carolina 27627

Telephone: (919) 854-1400

Facsimile: (919) 854-1401

Customer No. 20792

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Candi L. Riggs

Substitute form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	To Be Assigned
				Filing Date	Concurrently Herewith
				First Named Inventor	Joseph John Sumakeris
				Group Art Unit	
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	5308-2861

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
	1	US-6,472,677	B1	Rodriguez et al.	10-29-2002
	2	US-6,403,982	B2	Carter, Jr. et al.	06-11-2002
	3	US-6,396,080	B2	Carter, Jr. et al.	05-28-2002
	4	US-6,391,690	B2	Miyasaka	05-21-2002
	5	US-6,359,309	B1	Liao et al.	03-19-2002
	6	US 2001/0017374	A1	Carter, Jr. et al.	08-30-2001
	7	US-6,222,229	B1	Hebert et al.	04-24-2001
	8	US-6,218,680	B1	Carter, Jr. et al.	04-17-2001
	9	US-6,215,152	B1	Hebert	04-10-2001
	10	US-6,190,970	B1	Liao et al.	02-20-2001
	11	US-6,114,225		Liao et al.	09-05-2000
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	13	US-5,972,801		Lipkin et al.	10-26-1999
	14	US-5,698,891		Tomita et al.	12-16-1997
	15	US-5,506,421		Palmour	04-09-1996
	16	US-RE.34,861		Davis et al.	02-14-1995
	17	US-5,296,258		Tay et al.	03-22-1994
	18	US-5,164,359		Calviello et al.	11-17-1992
	19	US-5,160,696		Bowman	11-03-1992
	20	US-4,866,005		Davis et al.	09-12-1989
	21	US-4,766,482		Smeltzer et al.	08-23-1988
	22	US-4,260,448		Herzer	04-07-1981
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Office	Number	Kind Code (if known)		

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	23	Heissenstein et al., "Characterization of phosphorus doped <i>n</i> -type 6 <i>H</i> -silicon carbide epitaxial layers produced by nuclear transmutation doping," Journal of Applied Physics, Volume 83, Number 12, pp. 7542-7546, 15 June 1998	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.